

RoHS Compliant Product  
 A suffix of "-C" specifies halogen & lead-free

## DESCRIPTION

The SMS2312-C provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness. The SOT-23 package is universally preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

## FEATURES

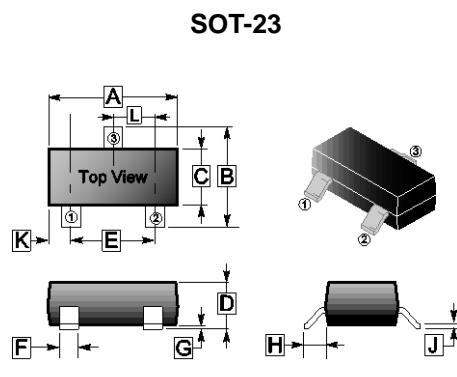
- Lower Gate Charge
- Simple Drive Requirement
- Fast Switching Characteristic

## MARKING

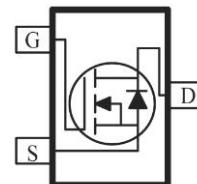
S12

## PACKAGE INFORMATION

Package	MPQ	Leader Size
SOT-23	3K	7 inch



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.65	3.10	G	0	0.18
B	2.10	3.00	H	0.55	REF.
C	1.10	1.80	J	0.08	0.26
D	0.89	1.40	K	0.60	REF.
E	1.70	2.30	L		0.95 TYP.
F	0.28	0.55			



## ORDER INFORMATION

Part Number	Type
SMS2312-C	Lead (Pb)-free and Halogen-free

## ABSOLUTE MAXIMUM RATINGS ( $T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 8$	V
Continuous Drain Current <sup>1</sup>	$I_D$	5	A
Pulsed Drain Current <sup>3</sup>	$I_{DM}$	20	A
Maximum Power Dissipation <sup>1</sup>	$P_D$	1.4	W
		0.9	
Operating Junction & Storage Temperature	$T_J, T_{STG}$	150, -55~150	°C
Thermal Resistance Ratings			
Thermal Resistance Junction-Ambient <sup>1</sup>	$R_{\theta JA}$	$t \leq 10\text{s}, 89$	°C/W
Thermal Resistance Junction-Ambient <sup>2</sup>		357	

**ELECTRICAL CHARACTERISTICS** ( $T_A=25^\circ\text{C}$  unless otherwise specified)

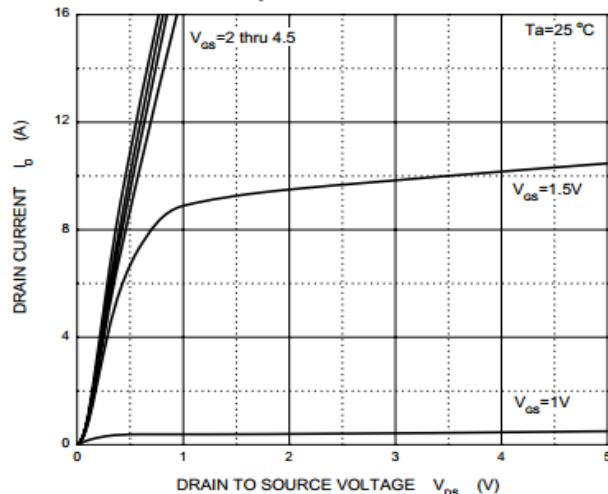
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage	$\text{BV}_{DSS}$	20	-	-	V	$\text{V}_{GS}=0, \text{I}_D=250\mu\text{A}$
Gate-Threshold Voltage	$\text{V}_{GS(\text{th})}$	0.45	-	1	V	$\text{V}_{DS}=\text{V}_{GS}, \text{I}_D=250\mu\text{A}$
Forward Transfer conductance	$\text{g}_{fs}$	6	-	-	S	$\text{V}_{DS}=10\text{V}, \text{I}_D=5\text{A}$
Gate-Source Leakage Current	$\text{I}_{GS}$	-	-	$\pm 100$	nA	$\text{V}_{GS}= \pm 8\text{V}, \text{V}_{DS}=0$
Drain-Source Leakage Current	$\text{I}_{DS}$	-	-	1	$\mu\text{A}$	$\text{V}_{DS}=20\text{V}, \text{V}_{GS}=0$
Static Drain-Source On-Resistance <sup>4</sup>	$\text{R}_{DS(\text{ON})}$	-	-	32	mΩ	$\text{V}_{GS}=4.5\text{V}, \text{I}_D=5\text{A}$
		-	-	36		$\text{V}_{GS}=2.5\text{V}, \text{I}_D=4.7\text{A}$
		-	-	42		$\text{V}_{GS}=1.8\text{V}, \text{I}_D=4.3\text{A}$
Gate Resistance	$\text{R}_g$	0.5	-	4.8	Ω	f=1MHz
Input Capacitance	$\text{C}_{iss}$	-	865	-	pF	$\text{V}_{GS}=0$ $\text{V}_{DS}=10\text{V}$ f=1MHz
Output Capacitance	$\text{C}_{oss}$	-	105	-		
Reverse Transfer Capacitance	$\text{C}_{rss}$	-	55	-		
Turn-on Delay Time	$\text{T}_{d(on)}$	-	10	-	nS	$\text{V}_{DD}=10\text{V}$ $\text{V}_{GEN}=5\text{V}$ $\text{R}_G=1\Omega$ $\text{R}_L=2.2\Omega$ $\text{I}_D=4\text{A}$
Rise Time	$\text{T}_r$	-	20	-		
Turn-off Delay Time	$\text{T}_{d(off)}$	-	32	-		
Fall Time	$\text{T}_f$	-	12	-		
<b>Source-Drain Diode</b>						
Diode Forward Voltage <sup>4</sup>	$\text{V}_{SD}$	-	0.75	1.2	V	$\text{I}_s=4\text{A}, \text{V}_{GS}=0$

Notes:

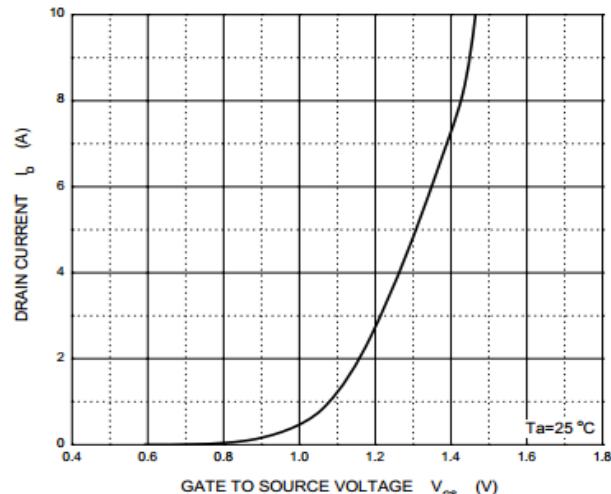
1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2oz copper.
2. Surface mounted on min. copper pad.
3. Pulse width limited by Max. junction temperature.
4. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%.

## CHARACTERISTIC CURVES

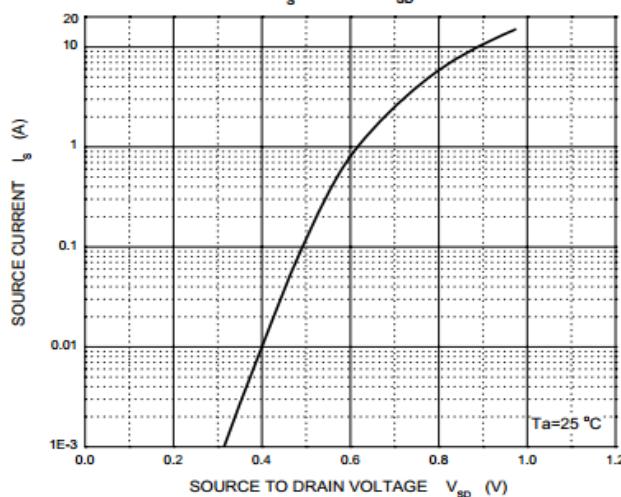
Output Characteristics



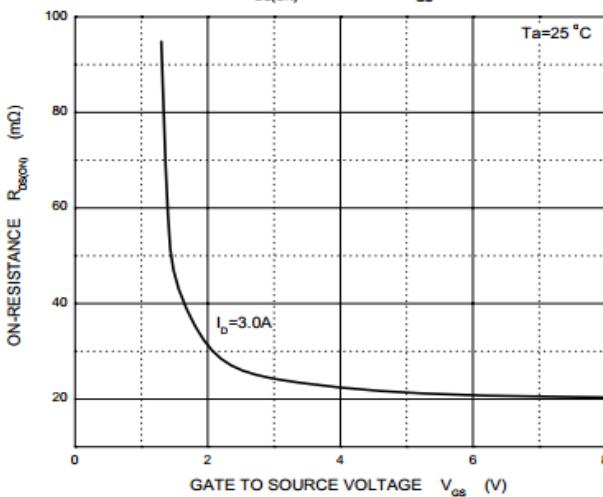
Transfer Characteristics



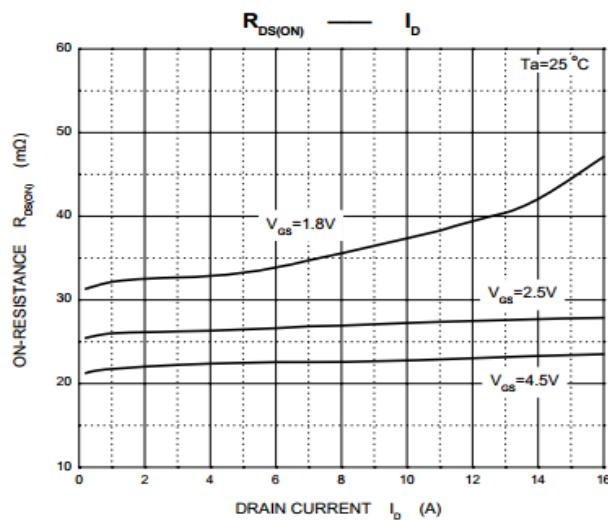
$I_s$  —  $V_{SD}$



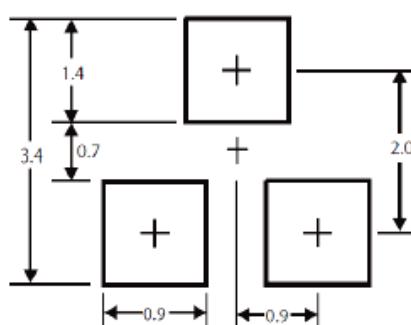
$R_{DS(ON)}$  —  $V_{GS}$



$R_{DS(ON)}$  —  $I_D$



Mounting Pad Layout



\*Dimensions in millimeters